









# CEB06N7

## 700V Δ 1.65Ω Δ 6A Δ Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

TO263 (D2PAK) package ▲ MSL 3

Super high dense cell density for extremely low R<sub>DS(ON)</sub>

High power and current handling capability

## **MAXIMUM RATINGS**

Parameter (T <sub>C</sub> = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V <sub>DS</sub>	700V
Gate-Source Voltage	V <sub>GS</sub>	±30V
Continuous Drain Current at T <sub>C</sub> = 25°C	I <sub>D</sub>	6A
Continuous Drain Current at T <sub>C</sub> = 100°C	I <sub>D</sub>	4A
Pulsed Drain Current Note 1	I <sub>DM</sub> Note 4	24A
Maximum Power Dissipation at T <sub>C</sub> = 25°C	P <sub>D</sub>	150W
Power Dissipation Derating above 25°C	$\Delta P_D$	1W/°C
Single Pulsed Avalanche Energy Note 5	E <sub>AS</sub>	125mJ
Single Pulsed Avalanche Current Note 5	I <sub>AS</sub>	5A
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +175°C

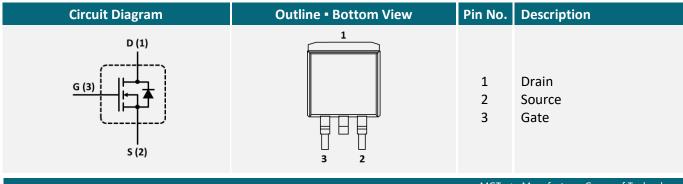
#### THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R <sub>TH_JC</sub>	1°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>TH JA</sub>	62.5°C/W

## **APPLICATIONS**

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
<b>₹</b>		-	PFC	*		

## **PIN DESCRIPTION**





## **ELECTRICAL CHARACTERISTICS** ▲ T<sub>C</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	700			V
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 30V$ , $V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -30V, V_{DS} = 0V$	$I_{GSSR}$			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_{D} = 250 \mu A$	$V_{GS(th)}$	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 3A$	R <sub>DS(ON)</sub>		1.65	2	Ω
Gate Input Resistance	f = 1MHz, Open Drain	R <sub>G</sub>		2		Ω
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS} = 25V$ , $V_{GS} = 0V$ , $f = 1MHz$	C <sub>ISS</sub>		1130		pF
Output Capacitance	$V_{DS} = 25V$ , $V_{GS} = 0V$ , $f = 1MHz$	Coss		115		pF
Reverse Transfer Capacitance	$V_{DS} = 25V$ , $V_{GS} = 0V$ , $f = 1MHz$	C <sub>RSS</sub>		20		pF
Switching Characteristics Note 3						
Turn-On Delay Time	$V_{DD} = 560V$ , $V_{GS} = 10V$ , $I_D = 5A$ , $R_{G(ext)} = 25\Omega$	t <sub>D(ON)</sub>		30		ns
Turn-On Rise Time	$V_{DD} = 560V$ , $V_{GS} = 10V$ , $I_D = 5A$ , $R_{G(ext)} = 25\Omega$	$t_R$		41		ns
Turn-Off Delay Time	$V_{DD}$ = 560V, $V_{GS}$ = 10V, $I_{D}$ = 5A, $R_{G(ext)}$ = 25 $\Omega$	t <sub>D(OFF)</sub>		77		ns
Turn-Off Fall Time	$V_{DD}$ = 560V, $V_{GS}$ = 10V, $I_D$ = 5A, $R_{G(ext)}$ = 25 $\Omega$	t <sub>F</sub>		42		ns
Total Gate Charge	$V_{DS} = 560V$ , $V_{GS} = 10V$ , $I_D = 5A$	$Q_{G}$		23		nC
Gate Source Charge	$V_{DS} = 560V$ , $V_{GS} = 10V$ , $I_D = 5A$	$Q_{GS}$		5		nC
Gate Drain Charge	$V_{DS} = 560V$ , $V_{GS} = 10V$ , $I_D = 5A$	$Q_{GD}$		8		nC
<b>Drain-Source Diode Characteristics a</b>	nd Maximum Ratings					
Drain-Source Diode Forward Current		Is			6	Α
Drain-Source Diode Forward Voltage Note 2	V <sub>GS</sub> = 0V, I <sub>S</sub> = 6A	$V_{SD}$			1.5	V

#### Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: Pulse width limited by safe operating area.
- 5: L = 6mH,  $I_{AS} = 3.6A$ ,  $V_{DD} = 50V$ ,  $R_G = 25Ω$ , Starting  $T_J = 25$ °C.



#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



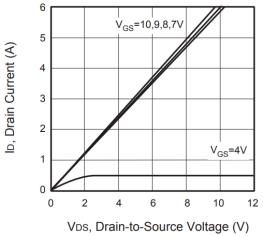


Fig. 2 • Transfer Characteristics

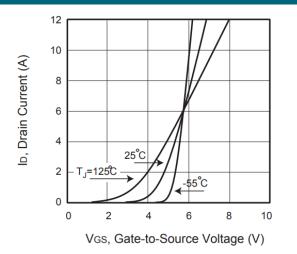


Fig. 3 • Capacitance

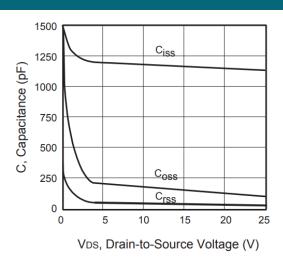


Fig. 4 • On-Resistance Variation with Temperature

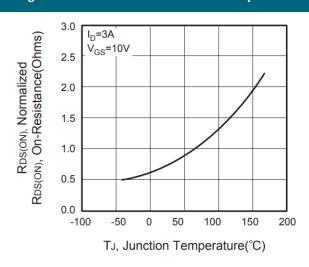


Fig. 5 - Gate Threshold Variation with Temperature

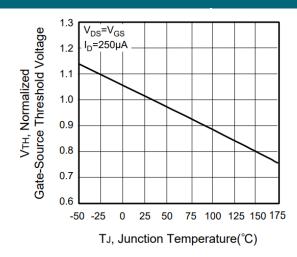
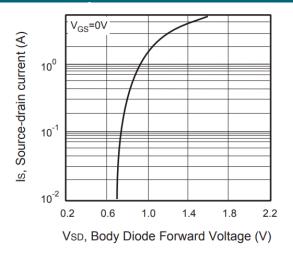


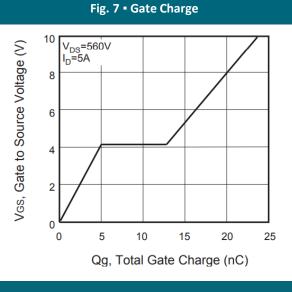
Fig. 6 • Body Diode Forward Voltage Variation with Source Current



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#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



R<sub>DS(ON)</sub>Limit 100ու

Fig. 8 • Maximum Safe Operating Area

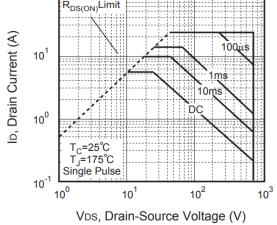
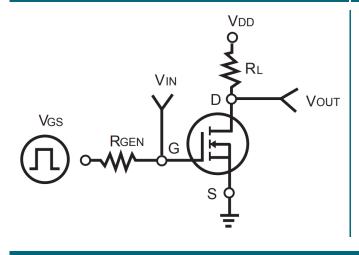


Fig. 9 • Switching Test Circuit

Fig. 10 • Switching Waveforms



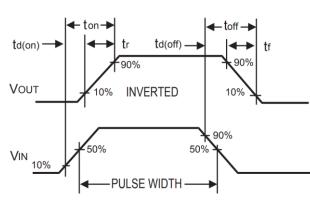
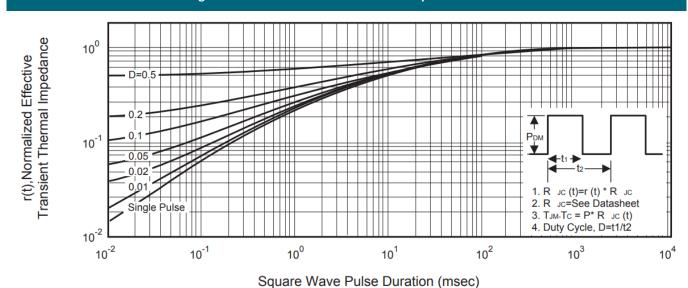
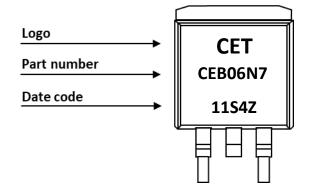


Fig. 11 - Normalized Thermal Transient Impedance Curve



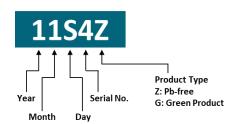


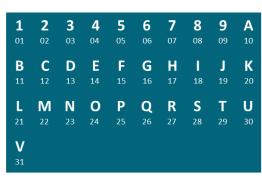
#### **PART MARKING**



## **DATE CODE**

Example: 11S4Z



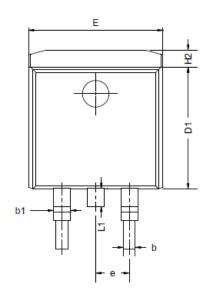


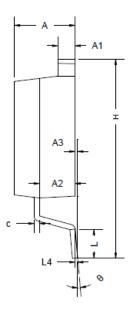
Coding list for "Day"

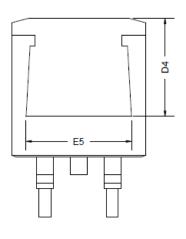


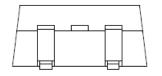


## **PACKAGE OUTLINE**









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
Α	4.37	4.57	4.77	
A1	1.22	1.27	1.42	
A2	2.49	2.69	2.89	
A3	0.00	0.13	0.25	
b	0.70	0.81	0.96	
b1	1.17	1.27	1.47	
С	0.30	0.38	0.53	
D1	8.50	8.70	8.90	
D4	6.60	-	-	

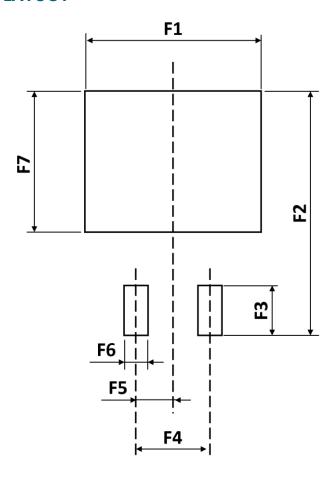
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)				
Е	9.86	10.16	10.36				
E5	7.06	-	-				
е	2.54 BSC						
Н	14.70	15.10	15.50				
H2	1.07	1.27	1.47				
L	2.00	2.30	2.60				
L1	1.40	1.55	1.70				
L4		0.25 BSC					
θ	0°	5°	9°				

## **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CEB06N7	TO263 (D2PAK)	Reel	800pcs	800pcs	6,400pcs	



## **RECOMMENDED PAD LAYOUT**



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	12.20	-
F2	-	16.90	-
F3	-	2.54	-
F4	-	5.08	-

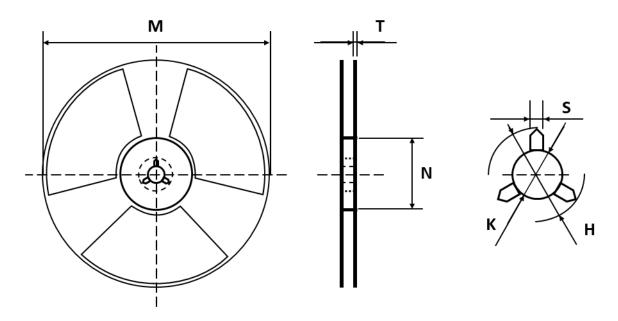
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	2.54	-
F6	-	1.60	-
F7	-	9.75	-

## Notes:

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

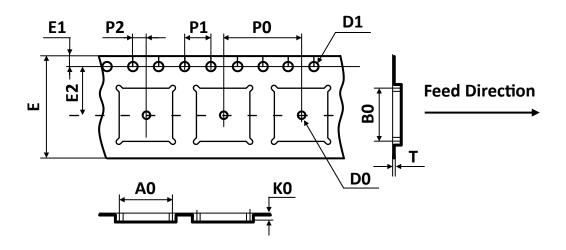


## **REEL DIMENSIONS** ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	H	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm	Ø330	±2.00	±0.50	+0.20	+0.50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

# **TAPE DIMENSIONS** ▲ All dimensions in mm

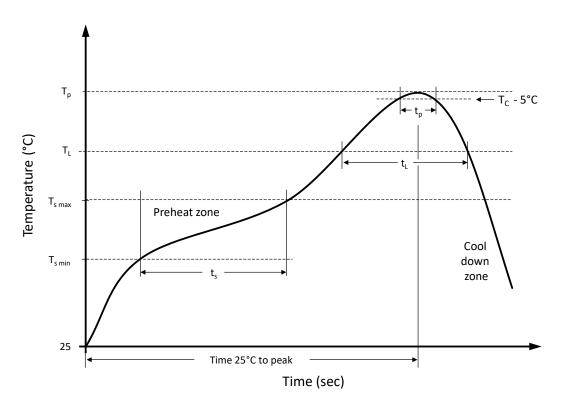


Package	Α0	В0	КО	D0	D1	E	E1	E2	P0	P1	P2	Т
TO263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D <sup>2</sup> PAK)	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

Note: All dimensions meet EIA-481-D requirements.



## RECOMMENDED REFLOW SOLDERING PROFILE



## **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T <sub>s max</sub>	150 °C	200 °C
Preheat time t <sub>s</sub> from T <sub>s min</sub> to T <sub>s max</sub>	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	$T_L$	183 °C	217 °C
Time t <sub>L</sub> maintained above T <sub>L</sub>	t <sub>L</sub>	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t <sub>p</sub>	20 seconds max.	30 seconds max.
Ramp-down rate (T <sub>L</sub> to T <sub>p</sub> )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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